

## **Pin Description**

Pin#	Pin Name	Туре	Pin Description
1	VDD	Power	VDD supplies the power for the operation of the power switch and internal control circuitry. Bypass the VDD pin to GND with a 0.1 $\mu$ F (or larger) capacitor.
2	ON	Input	A low-to-high transition on this pin initiates the operation of the SLG59M1563V's state machine. ON is a CMOS input with ON_V $_{\rm IL}$ < 0.3 V and ON_V $_{\rm IH}$ > 0.85 V thresholds. While there is an internal pull-down circuit to GND (~4 M $\Omega$ ), connect this pin directly to a general-purpose output (GPO) of a microcontroller, an application processor, or a system controller.
3, 4	D	MOSFET	Drain terminal connection of the n-channel MOSFET (2 pins fused for D). Connect at least a low-ESR 0.1 $\mu$ F capacitor from this pin to ground. Capacitors used at D should be rated at 10 V or higher.
5, 6	S	MOSFET	Source terminal connection of the n-channel MOSFET (2 pins fused for S). Connect a low-ESR capacitor from this pin to ground and consult the Electrical Characteristics table for recommended C <sub>LOAD</sub> range. Capacitors used at S should be rated at 10 V or higher.
7	PG	Output	A push pull output. PG is asserted HIGH when $V_S > 95\%$ of $V_D$ .
8	GND	GND	Ground connection. Connect this pin to system analog or power ground plane.

## **Ordering Information**

Part Number	Туре	Production Flow
SLG59M1563V	STDFN 8L	Industrial, -40 °C to 85 °C
SLG59M1563VTR	STDFN 8L (Tape and Reel)	Industrial, -40 °C to 85 °C



#### **Absolute Maximum Ratings**

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
V <sub>DD</sub>	Power Supply				7	V
T <sub>S</sub>	Storage Temperature		-65		150	°C
ESD <sub>HBM</sub>	ESD Protection	Human Body Model	2000			V
W <sub>DIS</sub>	Package Power Dissipation				0.4	W
MOSFET IDS <sub>PK</sub>	Peak Current from Drain to Source	For no more than 1 ms with 1% duty cycle		-	3.5	Α

Note: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

#### **Electrical Characteristics**

 $T_A$  = -40 °C to 85 °C unless otherwise noted. Typical values are at  $T_A$  = 25 °C, unless otherwise noted.

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
V <sub>DD</sub>	Power Supply Voltage	-40 °C to 85 °C	1.5		5.5	V
	Power Supply Current (PIN 1)	when OFF			1	μA
I <sub>DD</sub>	Fower Supply Current (FIN 1)	when ON, No load		14	30	μA
RDS <sub>ON</sub>	ON Resistance	T <sub>A</sub> = 25 °C; I <sub>DS</sub> = 100 mA		22.5	25	mΩ
KD30N	ON Nesistance	T <sub>A</sub> = 85 °C; I <sub>DS</sub> = 100 mA		25.6	30	mΩ
MOSFET IDS	Current from D to S	Continuous			2.5	Α
		$V_S$ = 1.0 V to 5.5 V, $V_D$ = 0 V, ON = 0 V; $V_{DD}$ = 1.5 V to 5.5 V; $T_A$ = 25 °C		0.04	0.55	μΑ
I <sub>REVERSE</sub>	MOSFET Reverse Leakage Current	$V_S = 1.0 \text{ V to } 5.5 \text{ V}, V_D = 0 \text{ V}, \text{ ON } = 0 \text{ V}$ $V_{DD} = 1.5 \text{ V to } 5.5 \text{ V}; T_A = 85 ^{\circ}\text{C}$		0.26	1.3	μА
		V <sub>S</sub> = 1.0 V to 5.5 V, V <sub>D</sub> = 0 V, ON = 0 V V <sub>DD</sub> = 1.5 V to 5.5 V; T <sub>A</sub> = -40 °C		0.31	5.5  1	μА
$V_{D}$	Drain Voltage		1.0		$V_{DD}$	V
T <sub>ON_Delay</sub>	ON Delay Time	50% ON to V <sub>S</sub> Ramp Start		300	500	μs
T <sub>Total_ON</sub>	Total Turn On Time	50% ON to 90% $V_S$ ; Example: $V_{DD} = V_D = 5 V$ , $C_{LOAD} = 10 \mu F$ , $R_{LOAD} = 20 \Omega$	2.1	2.6	3.1	ms
V <sub>S(SR)</sub>	Slew Rate	10% $V_S$ to 90% $V_S$ ; Example: $V_{DD} = V_D = 5 V$ , $C_{LOAD} = 10 \mu F$ , $R_{LOAD} = 20 \Omega$	1.4	1.95	2.2	V/ms
$C_{LOAD}$	Output Load Capacitance	C <sub>LOAD</sub> connected from S to GND			500	μF
ON_V <sub>IH</sub>	High Input Voltage on ON pin		0.85		$V_{DD}$	V
ON_V <sub>IL</sub>	Low Input Voltage on ON pin		-0.3	0	0.3	V
V <sub>OL</sub>	Low Output Voltage on PG pin	$V_{DD} = 5 \text{ V}, I_{OL} = -0.1 \text{ mA}$			0.4	V
V <sub>OH</sub>	High Output Voltage on PG pin	V <sub>DD</sub> = 5 V, I <sub>OH</sub> = 0.1 mA	V <sub>DD</sub> -0.4		$V_{DD}$	V
THERMON	Thermal shutoff turn-on temperature			125		°C
THERMOFF	Thermal shutoff turn-off temperature			100		°C
THERM <sub>TIME</sub>	Thermal shutoff time				1	ms
T <sub>OFF_Delay</sub>	OFF Delay Time	50% ON to $V_S$ Fall Start; $V_{DD}$ = $V_D$ = 5 V; $R_{LOAD}$ = 20 $\Omega$ ; no $C_{LOAD}$		8		μs

Datasheet Revision 1.03 11-Jan-2019

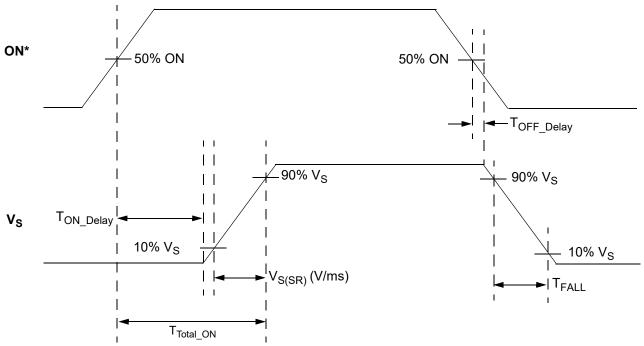


#### **Electrical Characteristics (continued)**

 $T_A$  = -40 °C to 85 °C unless otherwise noted. Typical values are at  $T_A$  = 25 °C, unless otherwise noted.

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
PG <sub>TRIGGER</sub>	Power Good Trigger Level	$V_S$ % of $V_D$		95		%

# $\rm T_{ON\_Delay}, \rm V_{S(SR)},$ and $\rm T_{Total\_ON}$ Timing Details

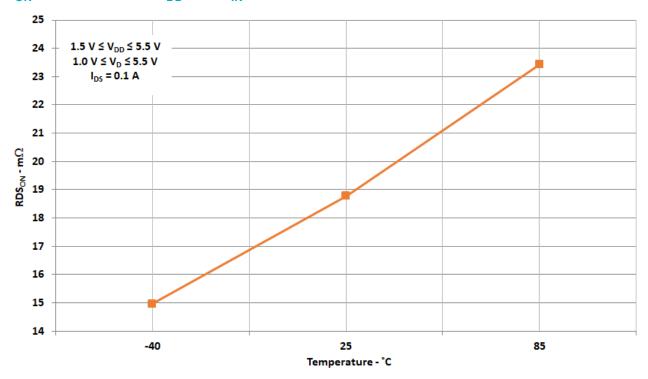


Note: \* Rise and Fall times of the ON signal are 100 ns



### **Typical Performance Characteristics**

## $RDS_{ON}$ vs. Temperature, $V_{DD}$ , and $V_{IN}$



### **SLG59M1563V**



An Ultra-small, 22.5 m $\Omega$ , 2.5 A Load Switch with Reverse Blocking

#### SLG59M1563V Power-Up/Power-Down Sequence Considerations

To ensure glitch-free power-up under all conditions, apply  $V_{DD}$  first, followed by  $V_{D}$  after  $V_{DD}$  exceeds 1 V. Then allow  $V_{D}$  to reach 90% of its max value before toggling the ON pin from Low-to-High. Likewise, power-down in reverse order.

If  $V_{DD}$  and  $V_{D}$  need to be powered up simultaneously, glitching can be minimized by having a suitable load capacitor. A 10  $\mu$ F  $C_{LOAD}$  will prevent glitches for rise times of  $V_{DD}$  and  $V_{D}$  less than 2 ms.

If the ON pin is toggled HIGH before  $V_{DD}$  and  $V_{D}$  have reached their steady-state values, the IPS timing parameters may differ from datasheet specifications.



#### **Layout Guidelines:**

- 1. The VDD pin needs a 0.1  $\mu$ F and 10  $\mu$ F external capacitors to smooth pulses from the power supply. Locate these capacitors as close as possible to the SLG59M1563V's PIN1.
- 2. Since the D and S pins dissipate most of the heat generated during high-load current operation, it is highly recommended to make power traces as short, direct, and wide as possible. A good practice is to make power traces with <u>absolute minimum widths</u> of 15 mils (0.381 mm) per Ampere. A representative layout, shown in Figure 1, illustrates proper techniques for heat to transfer as efficiently as possible out of the device;
- To minimize the effects of parasitic trace inductance on normal operation, it is recommended to connect input C<sub>IN</sub> and output C<sub>LOAD</sub> low-ESR capacitors as close as possible to the SLG59M1563V's D and S pins;
- 4. The GND pin should be connected to system analog or power ground plane.

#### SLG59M1563V Evaluation Board:

A GFET3 Evaluation Board for SLG59M1563V is designed according to the statements above and is illustrated on Figure 1. Please note that evaluation board has D\_Sense and S\_Sense pads. They cannot carry high currents and dedicated only for RDS<sub>ON</sub> evaluation.

Please solder your SLG59M1563V here

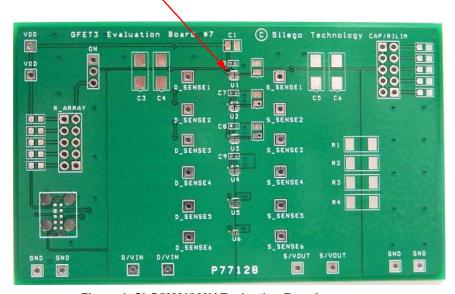


Figure 1. SLG59M1563V Evaluation Board.



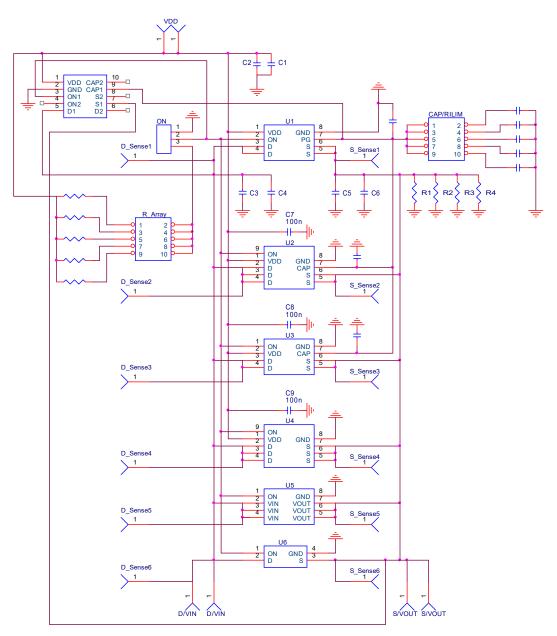


Figure 2. SLG59M1563V Evaluation Board Connection Circuit.



### **Basic Test Setup and Connections**

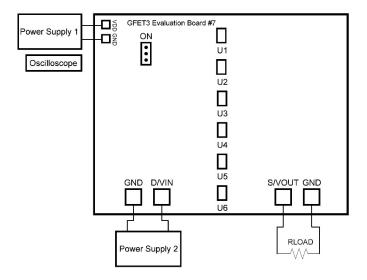


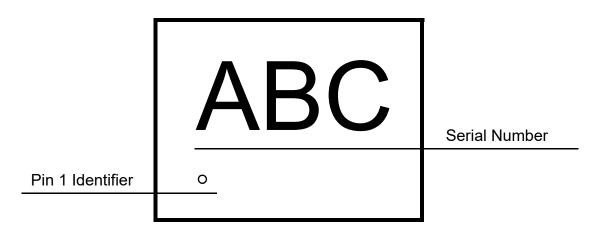
Figure 3. Typical connections for GFET3 Evaluation.

#### **EVB** Configuration

- 1. Connect oscilloscope probes to D/VIN, S/VOUT, ON, etc.;
- 2.Turn on Power Supply 1 and set desired  $V_{DD}$  from 1.5 V...5.5 V range;
- 3. Turn on Power Supply 2 and set desired  $V_D$  from 1  $V...V_{DD}$  range;
- 4.Toggle the ON signal High or Low to observe SLG59M1563V operation.



### **Package Top Marking System Definition**

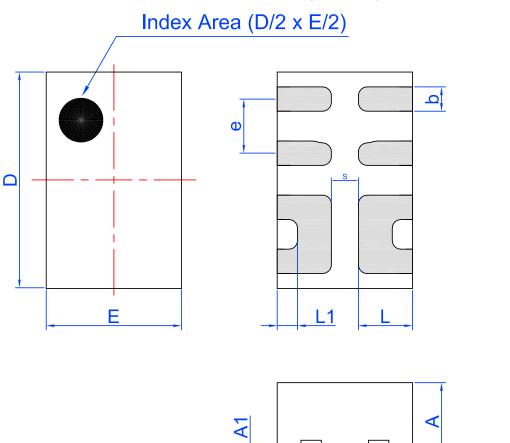


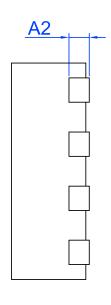
Each character in Serial Number field can be alphanumeric A-Z

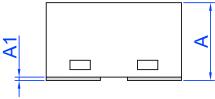


## **Package Drawing and Dimensions**

8 Lead STDFN Package 1.0 x 1.6 mm (Fused Lead) IC Net Weight: 0.0025 g







## Unit: mm

Symbol	Min	Nom.	Max	Symbol	Min	Nom.	Max
Α	0.50	0.55	0.60	D	1.55	1.60	1.65
A1	0.005	-	0.060	E	0.95	1.00	1.05
A2	0.10	0.15	0.20	L	0.35	0.40	0.45
b	0.13	0.18	0.23	L1	0.10	0.15	0.20
е	(	).40 BSC	,	S	(	),2 REF	

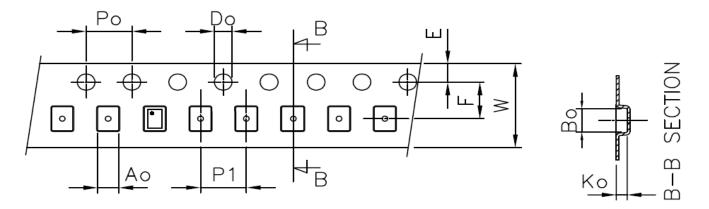


#### **Tape and Reel Specifications**

Dookogo	# of	Nominal Max Units		Units	Reel &	Leader (min)		Trailer (min)		Tape	Part
Package Type	Pins	Package Size [mm]	per Reel	per Box	Hub Size [mm]	Pockets	Length [mm]	Pockets	Length [mm]	Width [mm]	Pitch [mm]
STDFN 8L 1x1.6mm 0.4P FC Green		1.0 x 1.6 x 0.55	3,000	3,000	178 / 60	100	400	100	400	8	4

## **Carrier Tape Drawing and Dimensions**

Package Type	PocketBTM Length	PocketBTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge	Index Hole to Pocket Center	Tape Width
	A0	В0	K0	P0	P1	D0	E	F	W
STDFN 8L 1x1.6mm 0.4P FC Green	1.12	1.72	0.7	4	4	1.55	1.75	3.5	8



#### **Recommended Reflow Soldering Profile**

Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of 0.88 mm<sup>3</sup> (nominal). More information can be found at www.jedec.org.

## **SLG59M1563V**



An Ultra-small, 22.5 m $\Omega$ , 2.5 A Load Switch with Reverse Blocking

## **Revision History**

Date	Version	Change
1/11/2019	1.03	Updated Style and formatting Added Chart Added Layout Guidelines Fixed typos
9/13/2016	1.02	Added Power Up/Down Sequencing Considerations Updated text and parameter names for clarity
3/9/2016	1.01	Updated IDSlkg conditions

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